Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	206	(resistance adj measur\$4 adj bridge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON A	2006/10/17 07:17
L2	15	(resistance adj measur\$4 adj module)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:17
L3	15.	12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	<b>ON</b>	2006/10/17 07:17
L4	221	1 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:17
.L5	1	4 with terminal with output with circuit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:19
L6	2	4 with terminal with output not 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:20
L7 -	1	4 same (terminal with output with circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON -	2006/10/17 07:20
L8	3	4 same (terminal with output)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:21
L9	0	4 same (measurement with host)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:21

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L10	0	4 same (measurement same host)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:21
L11	2	4 same (measur\$4 with host)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:22
L12	0	4 same (measur\$4 same host) not 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:22
L13	79	4 same ((output circuit) with (measur\$4 terminal) with (host circuit module)) not 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; _IBM_TDB	OR	ON	2006/10/17 07:23
L14	3	4 same ((output circuit) with (measur\$4 terminal) with (host module)) not 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:23
L15	<b>i</b>	("6171378").PN.	USPAT; USOCR	OR:	OFF	2006/10/17 07:34
L16	0	L15 and anneal\$5 with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:34
L18	1	15 and (anneal\$4 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:35
L19	203	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:37
L20	10	L19 with (bridge module)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:42

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L21		2	L19 with (bridge module) and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:42
L22		2	L19 with (bridge module) and anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:43
L23		2	L19 with (bridge module) and (control\$4 with source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 07:58
L24	1	10	L19 with (bridge module) with feedback	US-PGPUB; USPAT;	OR	ON	2006/10/17 07:58
	*			EPO; JPO; DERWENT; IBM_TDB		,	
L25		2	(("6875950") or ("6146813")).PN.	USPAT; USOCR	OR	OFF	2006/10/17 08:15
L26		2	L25 and (compar\$4 reference database)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:16
L27		2	L25 and (compar\$4 reference data database)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:19
L28	- <i>·</i>	1	L25 and mov\$5 with support\$4	US-PGPUB;	OR	ON	2006/10/17 08:21
	•			-USPAT; EPO; JPO; DERWENT; IBM_TDB			
L29		·1	L25 and (laser with beam with control\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:23
L30	·	1	L25 and (excimer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:23
L31		1	("6875950").PN.	USPAT; USOCR	OR	OFF	2006/10/17 08:23

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L32	1	31 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:24
L33	97	(GSI lumonics) same excimer same laser	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2006/10/17 08:25
	t* :		IBM_TDB			
L34	0	(GSI lumonics) same excimer same laser same trim\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:25
L35	3	(GSI lumonics) same excimer same laser and (laser same trim\$4)	US-PGPUB; USPAT;	OR	ON	2006/10/17 08:25
			EPO; JPO; DERWENT; IBM_TDB			
S1	2	(("4943161") or ("5811763")).PN.	USPAT; USOCR	OR	OFF	2005/10/03 10:39
S2	2	(("4943161") or ("5811753")).PN.	USPAT; USOCR	OR	OFF	2005/10/03 12:37
S3	2	(("6875950") or ("6146813")).PN.	USPAT; USOCR	OR	OFF	2006/10/16 08:41
S4	174	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:38
S5	1	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7) with module	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:44
S6	2,	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7) and (resistance near9 module)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ÖN	2005/10/03 12:45
S7	38	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7) and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:48

S8	1	(resistance near5 measure\$5) with feedback with (control\$4 optimiz\$7) and (laser with anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:47
S9	1	(resistance near5 measure\$5) with	US-PGPUB;	OR.	ON	2005/10/03 12:59
	-	feedback with (control\$4 optimiz\$7) same laser	USPAT; EPO; JPO;	1 1	t	
	+-	Same laser	DERWENT;	ia, s, -	* * :	
			IBM_TDB			
S10	2	(resistance near5 measure\$5) with	US-PGPUB;	OR	ON	2005/10/03 13:02
		feedback with (control\$4 optimiz\$7)	USPAT;			
		same silicon	EPO; JPO; DERWENT;			
			IBM_TDB			
S11	- 1	(resistance near5 measure\$5) with	US-PGPUB;	OR	ON	2005/10/03 13:03
- 0	eggs of the el	feedback with (control\$4 optimiz\$7)	USPAT;			*
		same (silicon recrystal\$9 polysilic\$7 amorphous\$3) not S10	EPO; JPO; DERWENT;			
1			IBM_TDB	-		1 *
S12	1	laser with power with adjust\$4	US-PGPUB;	OR	ON	2006/07/11 10:10
		same anneal\$4 with trim\$4	USPAT;			, , ==
			EPO; JPO; DERWENT;			
			IBM_TDB			
S13	3	(laser same anneal\$4 same trim\$4)	US-PGPUB;	OR	ON	2006/07/11 10:21
		and (power with adjust\$4) and	USPAT;			
		(feedback "fed back" "feed back")	EPO; JPO; DERWENT;		-	
	i.	1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	IBM_TDB	A second		
S14	2	(("6875950") or ("6146813")).PN.	USPAT;	OR	OFF	2006/10/16 08:41
		en e	USOCR			
S15	0.	S14 and (anneal\$4 same trim\$4)	US-PGPUB;	OR	ON	2006/10/16 08:41
*** *			-USPAT; EPO, JPO;		4	
			DERWENT;	, 4,	,	
			IBM_TDB			
S16	16	laser with (anneal\$4 with trim\$4)	US-PGPUB;	OR	ON	2006/10/16 08:42
		with semiconduct\$4	USPAT; EPO; JPO;			
			DERWENT;			
			IBM_TDB	_		
S17	43	laser with (anneal\$4 with trim\$4)	US-PGPUB;	OR	ON	2006/10/16 08:43
		with (semiconduct\$4 resist\$4 capacit\$4 conduct\$5)	USPAT; EPO; JPO;			* - 2 - 4 - 6 - 1 - 7 -
		capacity i conductes)	DERWENT;		·· "	,
			IBM_TDB		) .	and the second second

		LASI Searc	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			
S18	9	S17 and amorphous with silicon with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:45
S19	9	S17 and amorphous with silicon with anneal\$5 with laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:47
S20	0	S19 and resistance with measur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:47
S21	7792	(polysilicon silicon wafer amorphous "thin film") same (resistance with measur\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:44
S22	14	(polysilicon silicon wafer amorphous "thin film") same (resistance with measur\$4) same (laser with anneal\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:54
S23	1	(laser with generat\$5) with (resistance with measur\$4) same (laser with anneal\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:58
S24	1	(laser with generat\$5) with (resistance with measur\$4) and (laser with anneal\$5) not S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:55
S25	53	(laser with generat\$5) with (resistance with measur\$4) not S23 not S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 08:58
S26	4	(laser with generat\$5) with (resistance with measur\$4) same (amorphous "thin film" polysilicon silicon) not S23 not S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 09:02
S27	16	laser same (sheet with resist\$4 with measur\$4) same (amorphous "thin film" polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:30

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S28	16	S27 not S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 09:04
S29	7	laser same (sheet with resist\$4 with measur\$4) same (amorphous "thin film" polysilicon silicon) same probe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR -	ON	2006/10/16 10:10
S30	2	laser same (sheet with resist\$4 with measur\$4) same (amorphous "thin film" polysilicon silicon) same probe same anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 10:29
S31	2	S14 and (measur\$5 with resist\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 10:30
S32	0	S14 and (measur\$5 with resist\$5) same anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 10:31
S33	0	S14 and (measur\$5 with resist\$5) and anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 10:31
S34	0	S14 and optim\$7 with feedback	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:31
S35	2	S14 and (optim\$7 feedback)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:31
S36	1	("6171378").PN.	USPAT; USOCR	OR	OFF	2006/10/17 07:33
S37	6347	(resistance with measur\$4 with terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:45

S38	117	(resistance with measur\$4 with terminal) with (electric\$4 near3 circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:46
S39	3	(resistance with measur\$4 with terminal) with (electric\$4 near3 circuit) same module	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:47
S40	15	(resistance adj measur\$4 adj module)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 08:14
S41	. 36	(host adj circuit adj module)	US-PGPUB;	OR	ON	2006/10/16 11:58
		, #	USPAT; EPO; JPO;			" OF
	u",		DERWENT; IBM_TDB			**
S42	3	(host adj circuit adj module) same (resistance near3 module)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:55
S43	<b>.</b> 0	(host adj circuit adj module) and (resistance near3 module) not S42	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2006/10/16 11:55
-	.). *		IBM_TDB			
S44	0	(host adj circuit near3 module) and (resistance near3 module) not S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:56
S45	0	(host adj circuit with module) same (resistance with module) not S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:56
S46	2	(host with circuit with module) same (resistance with module) not S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 11:56
S47	6	S41 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:00

S48	19	S41 and anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:01
S49	4	S41 and (anneal\$4 with (polysilicon, silicon wafer amorphous "thin film"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:02
S50	144	((circuit host) adj2 module) and (anneal\$4 with (polysilicon silicon wafer amorphous "thin film"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:03
S51	101	((circuit host) adj module) and (anneal\$4 with (polysilicon silicon wafer amorphous "thin film"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2006/10/16 12:03
S52	2	((circuit host) adj module) same (anneal\$4 with (polysilicon silicon wafer amorphous "thin film"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:04
S53	8	((circuit host) adj module) and (laser with anneal\$4 with (polysilicon silicon wafer amorphous "thin_film"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 12:04